

ILC5061

SOT-23 Power Supply reset Monitor



General Description

All-CMOS Monitor circuits in a 3-lead SOT-23 package offer the best performance in power consumption and accuracy.

The ILC5061 comes in a series of $\pm 1\%$ accurate trip voltages to fit most microprocessor applications. Even though its output can sink 2mA, the device draws only 1 μ A in normal operation.

Additionally, a built-in hysteresis of 5% of detect voltage simplifies system design.

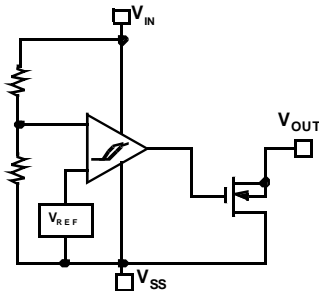
Features

- All-CMOS design in SOT-23 and SOT-89 package
- $\pm 1\%$ precision in Reset Detection
- Only 1 μ A of Iq
- 2mA of sink current capability
- Built-in hysteresis of 5% of detection voltage
- Voltage options of 2.6, 2.9, 3.1, 4.4, and 4.6V fit most supervisory applications

Applications

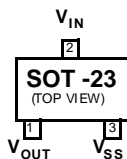
- Microprocessor reset circuits
- Memory battery back-up circuitry
- Power-on reset circuits
- Portable and battery powered electronics

Block Diagram



N-Channel Open Drain Output

Pin Package Configurations



Ordering Information*

ILC5061AM-26	2.6V $\pm 1\%$ Monitor in SOT-23
ILC5061AM-27	2.7V $\pm 1\%$ Monitor in SOT-23
ILC5061AM-28	2.8V $\pm 1\%$ Monitor in SOT-23
ILC5061AM-29	2.9V $\pm 1\%$ Monitor in SOT-23
ILC5061AM-31	3.1V $\pm 1\%$ Monitor in SOT-23
ILC5061AM-44	4.4V $\pm 1\%$ Monitor in SOT-23
ILC5061AM-46	4.6V $\pm 1\%$ Monitor in SOT-23
ILC5061M-26	2.6V $\pm 2\%$ Monitor in SOT-23
ILC5061M-27	2.7V $\pm 2\%$ Monitor in SOT-23
ILC5061M-28	2.8V $\pm 2\%$ Monitor in SOT-23
ILC5061M-29	2.9V $\pm 2\%$ Monitor in SOT-23
ILC5061M-31	3.1V $\pm 2\%$ Monitor in SOT-23
ILC5061M-44	4.4V $\pm 2\%$ Monitor in SOT-23
ILC5061M-46	4.6V $\pm 2\%$ Monitor in SOT-23

* Standard product offering comes in tape and reel, quantity 3000 per reel orientation right

Absolute Maximum Ratings (T_A=25°C)

Parameter	Symbol	Ratings	Units
Input Voltages	V _{IN}	12	V
Output Current	I _{OUT}	50	mA
Output Voltages	V _{OUT}	V _{SS} -0.3~+V _{IN} +0.3	V
Continuous Total Power Dissipation	SOT-23 P _d	150	mW
Operation Ambient temperature	T _{opr}	-30~+80	°C
Storage Temperature	T _{stg}	-40~+125	°C

Electrical Characteristics (T_A=25°C)

Parameter	Symbol	Conditions	Min	Type	Max	Units
Detect Fail Voltage	V _{DF}	A grade	V _{DF} X 0.99	V _{DF}	V _{DF} X 1.01	V
Detect Fail Voltage	V _{DF}	Standard grade	V _{DF} X 0.99	V _{DF}	V _{DF} X 1.02	V
Hysteresis Range	V _{HYS}		V _{DF} X 0.02	V _{DF} X 0.05	V _{DF} X 0.08	V
Supply Current	I _{SS}	V _{IN} = 1.5V V _{IN} = 2.0V V _{IN} = 3.0V V _{IN} = 4.0V V _{IN} = 5.0V		0.9 1.0 1.3 1.6 2.0	2.6 3.0 3.4 3.8 4.2	μA
Operating Voltage	V _{IN}	V _{DF} = 2.1~ 6.0V	1.5		10.0	V
Output Current	I _{OUT}	N-ch V _{DS} = 0.5V V _{IN} = 1.0V V _{IN} = 2.0V V _{IN} = 3.0V V _{IN} = 4.0V V _{IN} = 5.0V P-ch V _{DS} = 2.1V V _{IN} = 8V		2.2 7.7 10.1 11.5 13.0 -10		mA
Temperature Characteristics	ΔV _{DF} /(ΔT _{opr} •V _{DF})	30°C ≤ T _{opr} ≤ 80°C		±100		Ppm/°C
Delay Time Release Voltage → Output Inversion)	T _{DLY} (V _{DR} → V _{OUT} inversion)				0.2	ms
Note: 1. An additional resistor between the V _{IN} pin and supply voltage may cause deterioration of the characteristics due to increasing V _{DR} .						

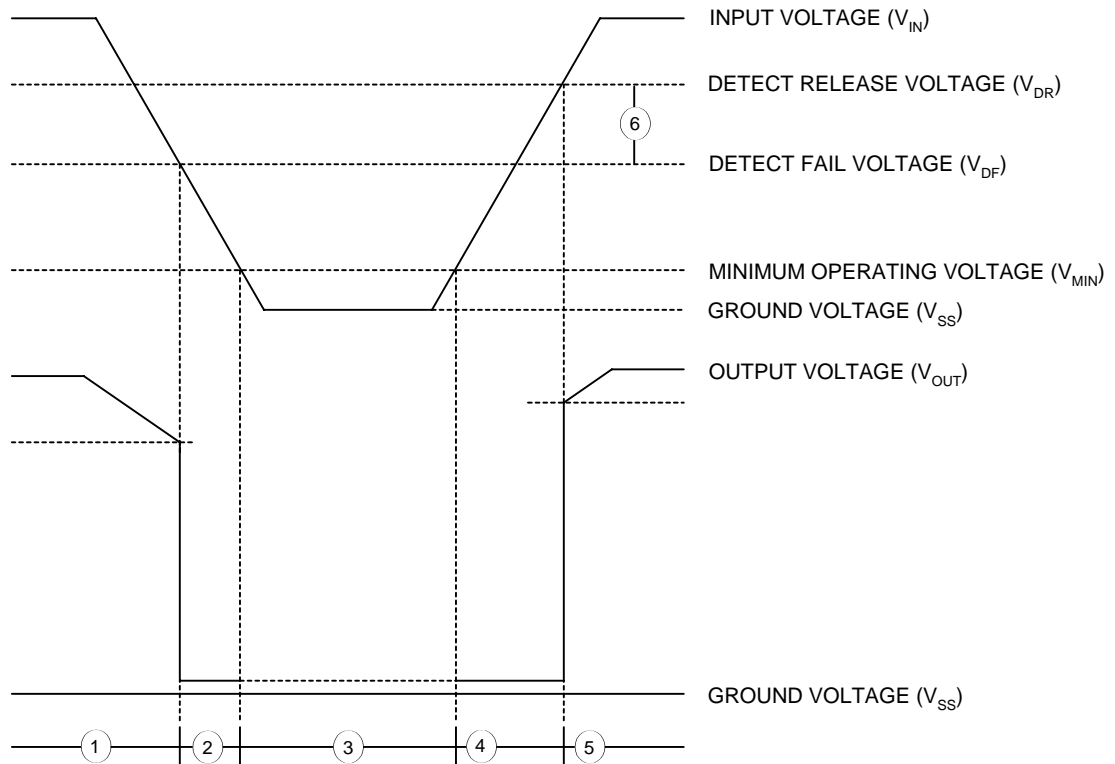
Functional Description

The following designators 1~6 refer to the timing diagram below.

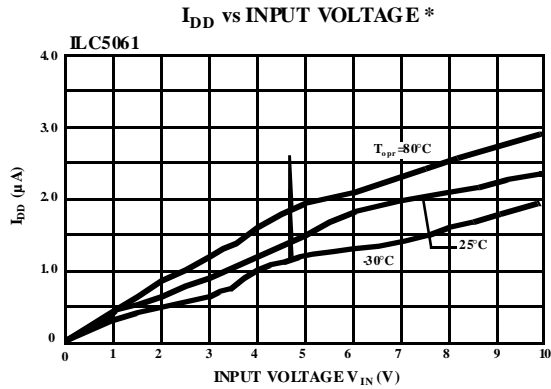
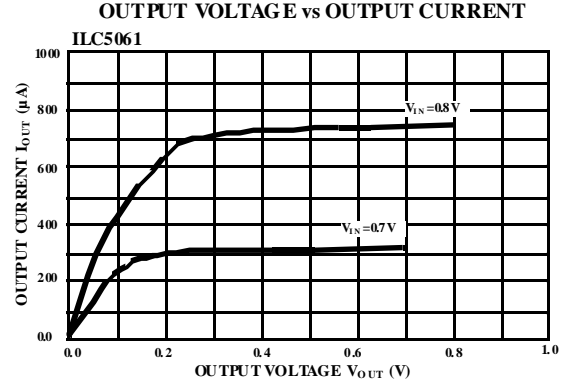
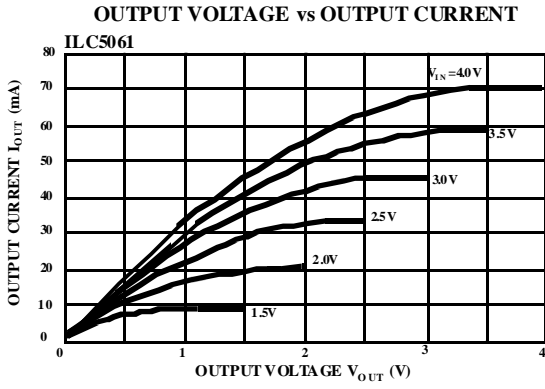
1. While the input voltage (V_{IN}) is higher than the detect voltage (V_{DF}), the V_{OUT} output pin is at high impedance state.
2. When the input V_{IN} voltage falls lower than V_{DF} , V_{OUT} drops near to ground voltage
3. If the input voltage further decreases below the minimum operating voltage (V_{MIN}), the V_{OUT} output becomes unstable. In this condition, if the V_{OUT} pin is pulled up, V_{OUT} indicates the V_{IN} voltage.

4. During an increase of the input voltage from the V_{SS} voltage, V_{OUT} is not stable in the voltage below the V_{MIN} . Exceeding that level, the output stays at the ground level (V_{SS}) between the minimum operating voltage (V_{MIN}) and the detect release voltage (V_{DR}).
5. If the input voltage increases more than V_{DR} , then the V_{OUT} output pin is at high impedance state.
6. The difference between V_{DR} and V_{DF} is the hysteresis in the system.

Timing Diagram



Typical Performance Characteristics - general conditions for all curves



* A spike of 1/2 to 1 μA may appear as V_{in} crosses V_{DR} or V_{DF}

